

Abstract

A method of forming a vapor deposited film of a silicon oxide on the surface of a substrate by holding
5 the substrate to be treated in a plasma-treating chamber, and effecting the treatment with a chemical plasma by feeding an organosilicon compound and an oxidizing gas into the treating chamber, wherein the rate of feeding the oxidizing gas is varied while
10 maintaining constant the rate of feeding the organosilicon compound gas into the plasma-treating chamber during the formation of the vapor deposited film. A chemical vapor deposited film is formed featuring excellent adhesiveness, softness,
15 flexibility, oxygen-barrier property and water-barrier property.

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